National Semiconductor

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LP38856
3A Fast-Response High-Accuracy LDO Linear Regulator with Enable

General Description

The LP38856 is a high-current, fast-response regulator which can maintain output voltage regulation with an extremely low input to output voltage drop. Fabricated on a CMOS process, the device operates from two input voltages: V_{BIAS} provides power for the internal bias and control circuits, as well as drive for the gate of the N-MOS power transistor, while V_{IN} supplies power to the load. The use of an external bias rail allows the part to operate from ultra low V_{IN} voltages. Unlike bipolar regulators, the CMOS architecture consumes extremely low quiescent current at any output load current. The use of an N-MOS power transistor results in wide bandwidth, yet minimum external capacitance is required to maintain loop stability.

The fast transient response of this device makes it suitable for use in powering DSP, Microcontroller Core voltages and Switch Mode Power Supply post regulators. The LP38856 is available in TO-220 and TO-263 5-Lead packages.

Dropout Voltage: 240 mV (typical) at 3A load current.

Low Ground Pin Current: 14 mA (typical) at 3A load current.

Shutdown Current: 1 µA (typical) $I_{IN(GND)}$ when EN pin is low.

Precision Output Voltage: ±1.0% for T_J = 25˚C and ±2.0% for 0˚C ≤ T_J ≤ +125˚C, across all line and load conditions

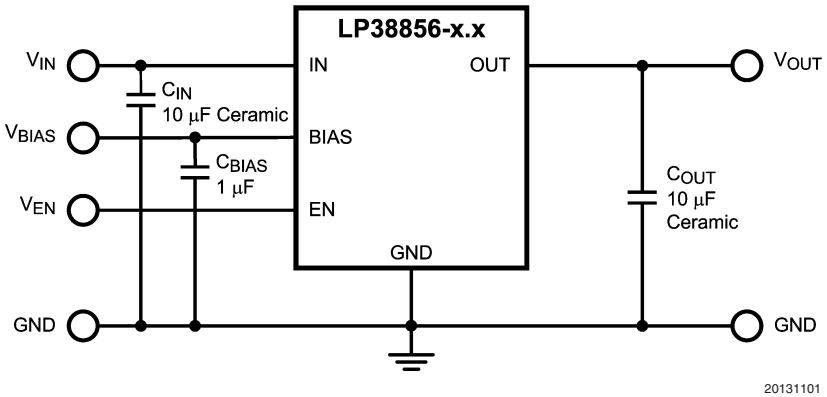
Features

- Standard V_{OUT} values of 0.8V and 1.2V
- Stable with 10 µF ceramic capacitors
- Dropout voltage of 240 mV (typical) at 3A load current
- Precision Output Voltage across all line and load conditions:
  - — ±1.0% for T_J = 25˚C
  - — ±2.0% for 0˚C ≤ T_J ≤ +125˚C
  - — ±3.0% for -40˚C ≤ T_J ≤ +125˚C
- Over-Temperature and Over-Current protection
- Available in 5 lead TO-220 and TO-263 packages
- Custom V_{OUT} values between 0.8V and 1.2V are available
- -40˚C to +125˚C Operating Temperature Range

Applications

- ASIC Power Supplies In:
  - Desktops, Notebooks, and Graphics Cards, Servers
  - Gaming Set Top Boxes, Printers and Copiers
- Server Core and I/O Supplies
- DSP and FPGA Power Supplies
- SMPS Post-Regulator

Typical Application Circuit

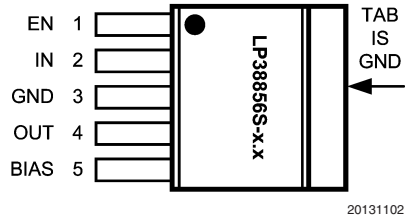


Ordering Information

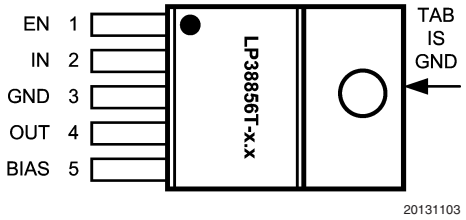
V_{OUT} *	Order Number	Package Type	Package Drawing	Supplied As
0.8V	LP38856S-0.8	TO263-5	TS5B	Rail of 45
	LP38856SX-0.8	TO263-5	TS5B	Tape and Reel of 500
	LP38856T-0.8	TO220-5	T05D	Rail of 45
1.2V	LP38856S-1.2	TO263-5	TS5B	Rail of 45
	LP38856SX-1.2	TO263-5	TS5B	Tape and Reel of 500
	LP38856T-1.2	TO220-5	T05D	Rail of 45

* For custom V_{OUT} values between 0.8V and 1.2V please contact the National Semiconductor Sales Office.

Connection Diagrams



TO-263, Top View



TO-220, Top View

Pin Descriptions

TO220–5 and TO263–5 Packages

Pin #	Pin Symbol	Pin Description
1	EN	The device Enable pin.
2	IN	The unregulated input voltage pin
3	GND	Ground
4	OUT	The regulated output voltage pin
5	BIAS	The supply for the internal control and reference circuitry
TAB	TAB	The TAB is a thermal connection that is physically attached to the backside of the die, and is used as a thermal heat-sink connection. See the Application Information section for details

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature Range	−65˚C to +150˚C
Lead Temperature	
Soldering, 5 seconds	260˚C
ESD Rating	
Human Body Model (Note 2)	±2 kV
Power Dissipation (Note 3)	Internally Limited
V_{IN} Supply Voltage (Survival)	−0.3V to +6.0V
V_{BIAS} Supply Voltage (Survival)	−0.3V to +6.0V
V_{EN} Voltage (Survival)	−0.3V to +6.0V
V_{OUT} Voltage (Survival)	−0.3V to +6.0V
I_{OUT} Current (Survival)	Internally Limited
Junction Temperature	−40˚C to +150˚C

Operating Ratings (Note 1)

V_{IN} Supply Voltage	(V_{OUT} + V_{DO}) to V_{BIAS}
V_{BIAS} Supply Voltage	3.0V to 5.5V
V_{EN} Enable Input Voltage	0.0V to V_{BIAS}
I_{OUT}	0 mA to 3.0A
Junction Temperature Range(Note 3)	−40˚C to +125˚C

Electrical Characteristics

Unless otherwise specified: $V_{IN} = V_{OUT(NOM)} + 1V$, V_{BIAS} = 3.0V, I_{OUT} = 10 mA, $C_{IN} = C_{OUT}$ = 10 µF, C_{BIAS} = 1µF, $V_{EN} = V_{BIAS}$. Limits in standard type are for T_J = 25˚C only; limits in **boldface type** apply over the junction temperature (T_J) range of -40˚C to +125˚C. Minimum and Maximum limits are guaranteed through test, design, or statistical correlation. Typical values represent the most likely parametric norm at T_J = 25˚C, and are provided for reference purposes only.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Units
V_{OUT}	Output Voltage Tolerance	$V_{OUT(NOM)} + 1V \le V_{IN} \le V_{BIAS}$, 3.0V ≤ V_{BIAS} ≤ 5.5V, 10 mA ≤ I_{OUT} ≤ 3.0A	-1.0 **-3.0**	0.0	+1.0 **+3.0**	%
		$V_{OUT(NOM)} + 1V \le V_{IN} \le V_{BIAS}$, 3.0V ≤ V_{BIAS} ≤ 5.5V, 10 mA ≤ I_{OUT} ≤ 3.0A, 0˚C ≤ T_J ≤ 125˚C	-2.0	0	+2.0	
$\Delta V_{OUT}/\Delta V_{IN}$	Line Regulation, V_{IN} (Note 4)	$V_{OUT(NOM)} + 1V \le V_{IN} \le V_{BIAS}$	-	0.04	-	%/V
$\Delta V_{OUT}/\Delta V_{BIAS}$	Line Regulation, V_{BIAS} (Note 4)	3.0V ≤ V_{BIAS} ≤ 5.5V	-	0.10	-	%/V
$\Delta V_{OUT}/\Delta I_{OUT}$	Output Voltage Load Regulation (Note 5)	10 mA ≤ I_{OUT} ≤ 3.0A	-	0.2	-	%/A
V_{DO}	Dropout Voltage $V_{IN} - V_{OUT}$ (Note 6)	I_{OUT} = 3.0A	-	240	300 **450**	mV
$I_{GND(IN)}$	Ground Pin Current Drawn from V_{IN} Supply	LP38856-0.8 10 mA ≤ I_{OUT} ≤ 3.0A	-	7.0	8.5 **9.0**	mA
		LP38856-1.2 10 mA ≤ I_{OUT} ≤ 3.0A	-	11	12 **15**	
		V_{EN} ≤ 0.5V	-	1.0	10 **300**	µA
$I_{GND(BIAS)}$	Ground Pin Current Drawn from V_{BIAS} Supply	10 mA ≤ I_{OUT} ≤ 3.0A	-	3.0	3.8 **4.5**	mA
		V_{EN} ≤ 0.5V	-	100	170 **200**	µA
UVLO	Under-Voltage Lock-Out Threshold	V_{BIAS} rising until device is functional	2.20 **2.00**	2.45	2.70 **2.90**	V
$UVLO_{(HYS)}$	Under-Voltage Lock-Out Hysteresis	V_{BIAS} falling from UVLO threshold until device is non-functional	60 **50**	150	300 **350**	mV
I_{SC}	Output Short-Circuit Current	$V_{IN} = V_{OUT(NOM)} + 1V$, V_{BIAS} = 3.0V, V_{OUT} = 0.0V	-	6.2	-	A

Electrical Characteristics

Unless otherwise specified: $V_{IN} = V_{OUT(NOM)} + 1V$, $V_{BIAS} = 3.0V$, $I_{OUT} = 10$ mA, $C_{IN} = C_{OUT} = 10$ µF, $C_{BIAS} = 1$µF, $V_{EN} = V_{BIAS}$. Limits in standard type are for $T_J = 25$˚C only; limits in **boldface type** apply over the junction temperature (T_J) range of -40˚C to +125˚C. Minimum and Maximum limits are guaranteed through test, design, or statistical correlation. Typical values represent the most likely parametric norm at $T_J = 25$˚C, and are provided for reference purposes only. (Continued)

Symbol	Parameter	Conditions	MIN	TYP	MAX	Units
ENABLE Pin						
I_{EN}	ENABLE pin Current	$V_{EN} = V_{BIAS}$	-	0.01	-	µA
		$V_{EN} = 0.0V$, $V_{BIAS} = 5.5V$	-19 **-13**	-30	-40 **-51**	
$V_{EN(ON)}$	Enable Voltage Threshold	V_{EN} rising until Output = ON	1.00 **0.90**	1.25	1.50 **1.55**	V
$V_{EN(HYS)}$	Enable Voltage Hysteresis	V_{EN} falling from $V_{EN(ON)}$ until Output = OFF	50 **30**	100	150 **200**	mV
t_{OFF}	Turn-OFF Delay Time	$R_{LOAD} \times C_{OUT} << t_{OFF}$	-	20	-	µs
t_{ON}	Turn-ON Delay Time	$R_{LOAD} \times C_{OUT} << t_{ON}$	-	15	-	
AC Parameters						
PSRR (V_{IN})	Ripple Rejection for V_{IN} Input Voltage	$V_{IN} = V_{OUT} + 1V$, f = 120 Hz	-	80	-	dB
		$V_{IN} = V_{OUT} + 1V$, f = 1 kHz	-	65	-	
PSRR (V_{BIAS})	Ripple Rejection for V_{BIAS} Voltage	$V_{BIAS} = V_{OUT} + 3V$, f = 120 Hz	-	58	-	dB
		$V_{BIAS} = V_{OUT} + 3V$, f = 1 kHz	-	58	-	
e_n	Output Noise Density	f = 120 Hz	-	1	-	µV/$\sqrt{Hz}$
	Output Noise Voltage	BW = 10 Hz – 100 kHz	-	150	-	µV (rms)
		BW = 300 Hz – 300 kHz	-	90	-	
Thermal Parameters						
T_{SD}	Thermal Shutdown Junction Temperature		-	160	-	˚C
$T_{SD(HYS)}$	Thermal Shutdown Hysteresis		-	10	-	
θ_{JA}	Thermal Resistance, Junction to Ambient(Note 3)	TO220-5	-	60	-	˚C/W
		TO263-5	-	60	-	
θ_{JC}	Thermal Resistance, Junction to Case(Note 3)	TO220-5	-	3	-	
		TO263-5	-	3	-	

Note 1: Absolute maximum ratings indicate limits beyond which damage to the component may occur. Operating ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications, see Electrical Characteristics. Specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: The Human Body Model (HBM) is a 100 pF capacitor discharged through a 1.5k resistor into each pin. Test method is per JESD22-A114. The HBM rating for device pin 1 (EN) is ±1.5 kV.

Note 3: Device power dissipation must be de-rated based on device power dissipation (T_D), ambient temperature (T_A), and package junction to ambient thermal resistance (θ_{JA}). Additional heat-sinking may be required to ensure that the device junction temperature (T_J) does not exceed the maximum operating rating. See the Application Information section for details.

Note 4: Output voltage line regulation is defined as the change in output voltage from nominal value resulting from a change in input voltage.

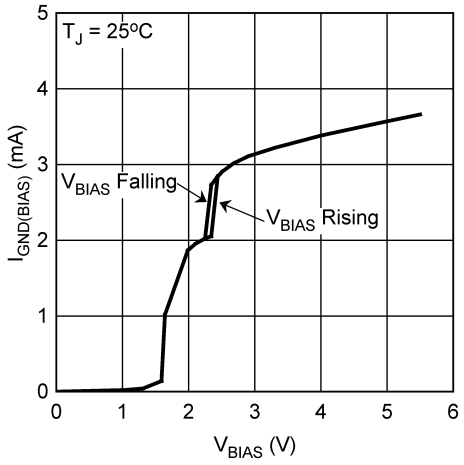
Note 5: Output voltage load regulation is defined as the change in output voltage from nominal value as the load current increases from no load to full load.

Note 6: Dropout voltage is defined the as input to output voltage differential ($V_{IN} - V_{OUT}$) where the input voltage is low enough to cause the output voltage to drop no more than 2% from the nominal value

Typical Performance Characteristics

Unless otherwise specified: T_J = 25˚C, V_{IN} = $V_{OUT(NOM)}$ + 1V, V_{BIAS} = 3.0V, I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 10 µF Ceramic, C_{BIAS} = 1 µF Ceramic, V_{EN} = V_{BIAS}.

V_{BIAS} Ground Pin Current ($I_{GND(BIAS)}$) vs V_{BIAS}



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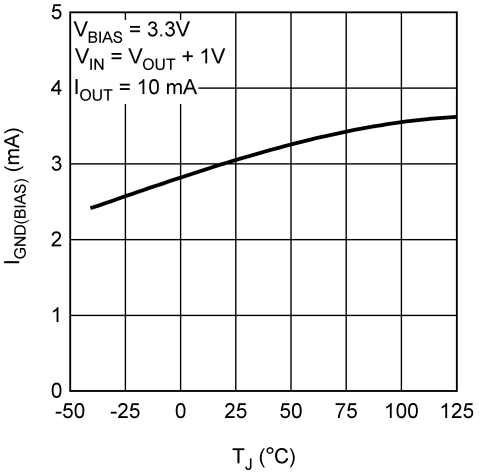
V_{BIAS} Ground Pin Current ($I_{GND(BIAS)}$) vs Temperature



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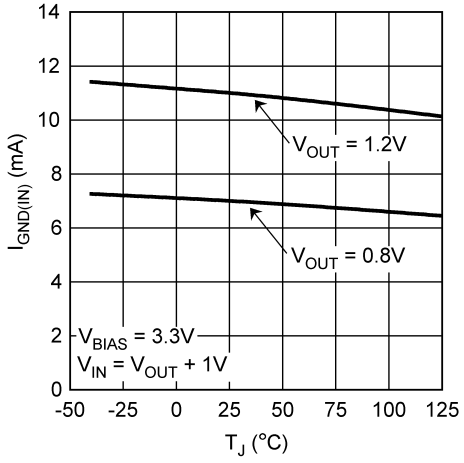
V_{IN} Ground Pin Current ($I_{GND(IN)}$) vs Temperature



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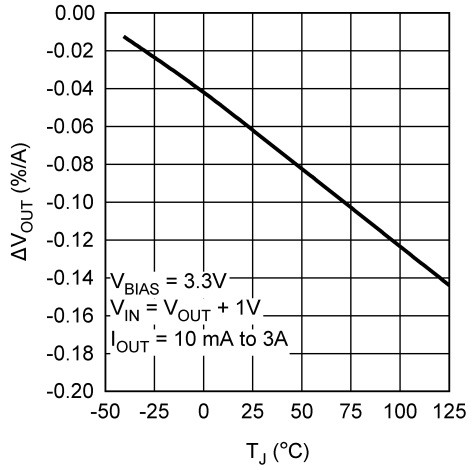
Load Regulation vs Temperature



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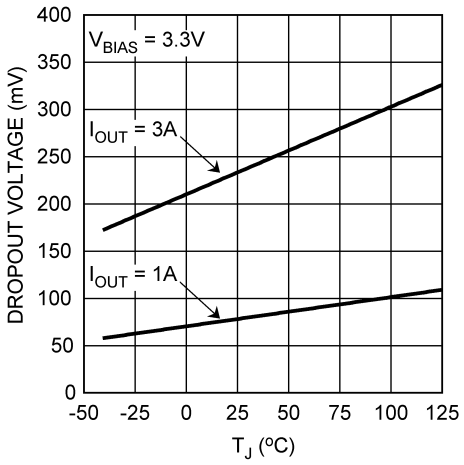
Dropout Voltage (V_{DO}) vs Temperature



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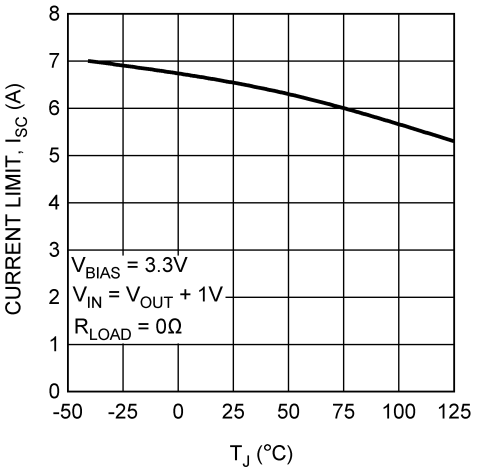
Output Current Limit (I_{SC}) vs Temperature



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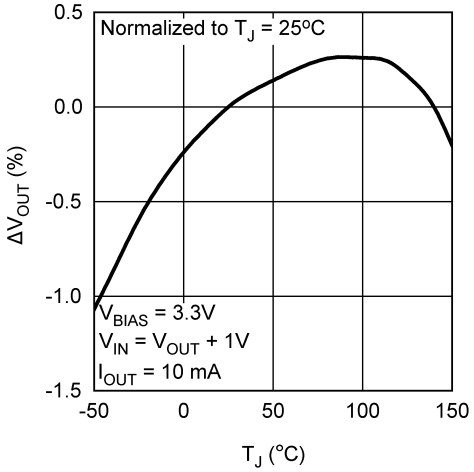
Typical Performance Characteristics

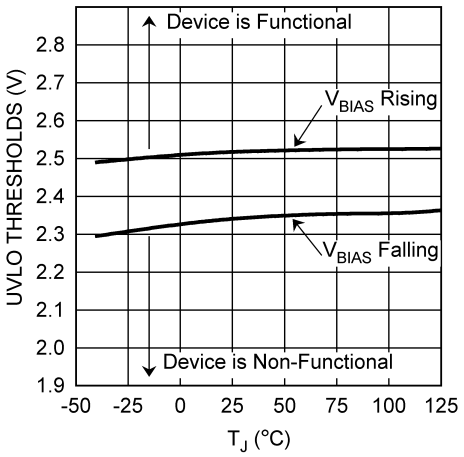
Unless otherwise specified: T_J = 25˚C, V_{IN} = $V_{OUT(NOM)}$ + 1V, V_{BIAS} = 3.0V, I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 10 µF Ceramic, C_{BIAS} = 1 µF Ceramic, V_{EN} = V_{BIAS}. (Continued)

V_{OUT} vs Temperature



20131167

UVLO Thresholds vs Temperature



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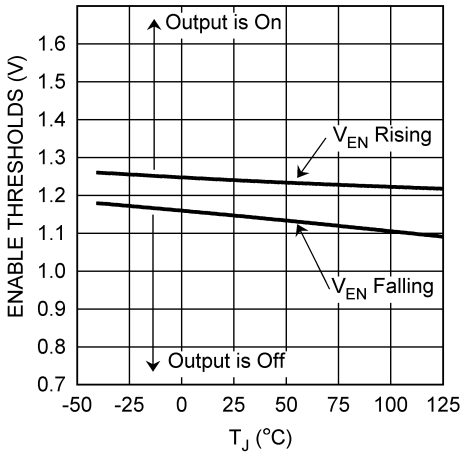
Enable Thresholds (V_{EN}) vs Temperature



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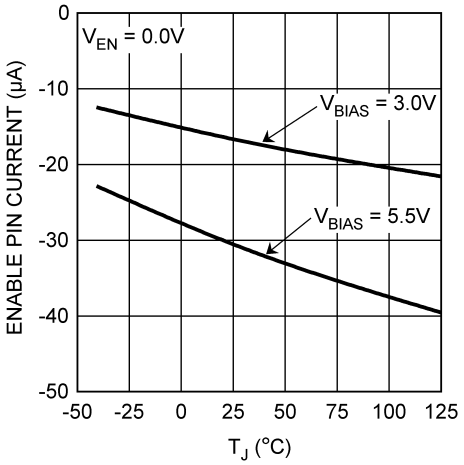
Enable Pull-Down Current (I_{EN}) vs Temperature



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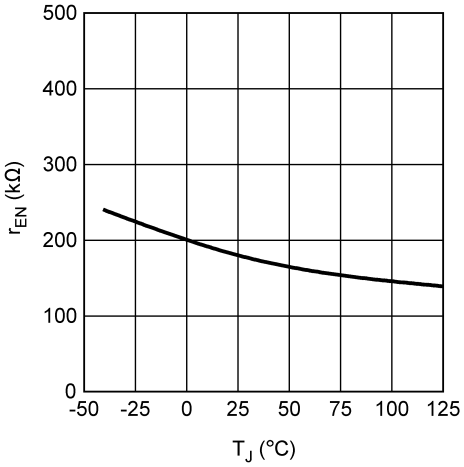
Enable Pull-Up Resistor (r_{EN}) vs Temperature



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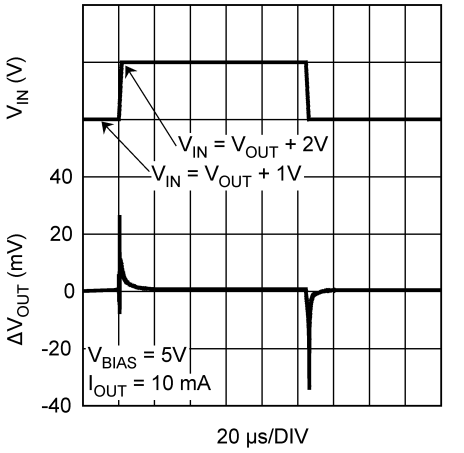
V_{IN} Line Transient Response

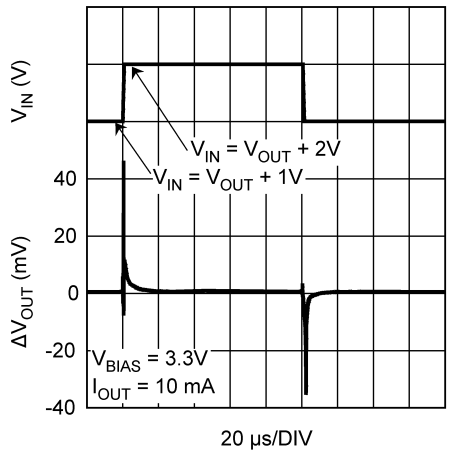


20131177

Typical Performance Characteristics

Unless otherwise specified: T_J = 25˚C, V_{IN} = $V_{OUT(NOM)}$ + 1V, V_{BIAS} = 3.0V, I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 10 µF Ceramic, C_{BIAS} = 1 µF Ceramic, V_{EN} = V_{BIAS}. (Continued)

V_{IN} Line Transient Response



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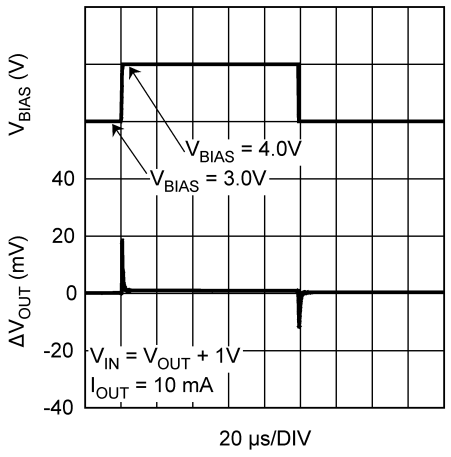
V_{BIAS} Line Transient Response



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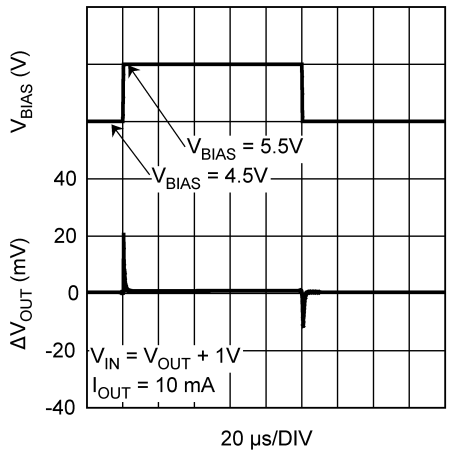
V_{BIAS} Line Transient Response



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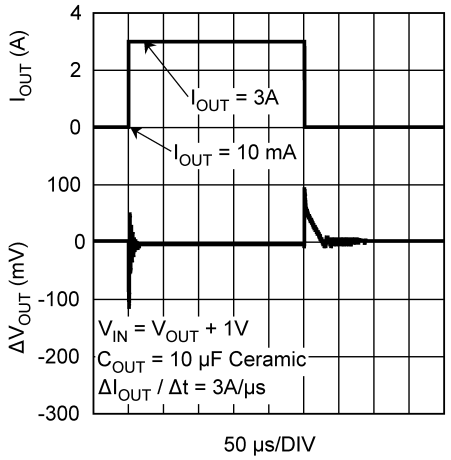
Load Transient Response, C_{OUT} = 10 µF Ceramic



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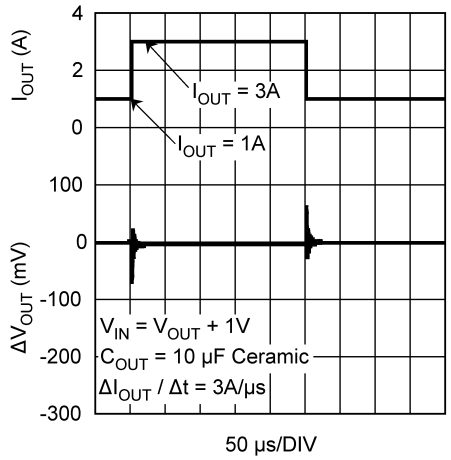
Load Transient Respose, C_{OUT} = 10 µF Ceramic



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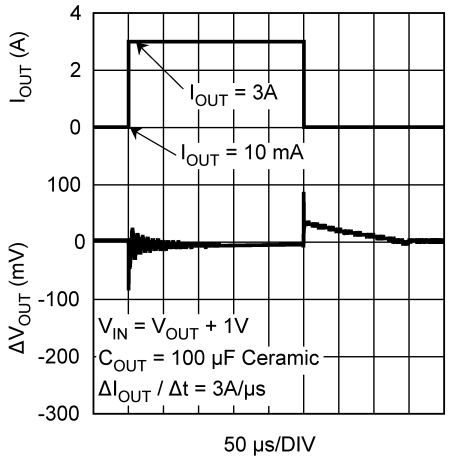
Load Transient Response, C_{OUT} = 100 µF Ceramic

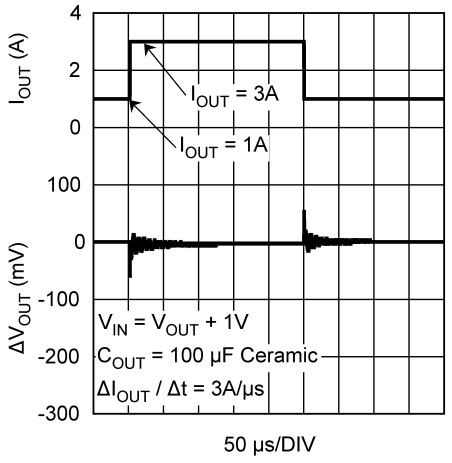


20131183

Typical Performance Characteristics

Unless otherwise specified: T_J = 25˚C, V_{IN} = $V_{OUT(NOM)}$ + 1V, V_{BIAS} = 3.0V, I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 10 µF Ceramic, C_{BIAS} = 1 µF Ceramic, V_{EN} = V_{BIAS}. (Continued)

Load Transient Response, C_{OUT} = 100 µF Ceramic



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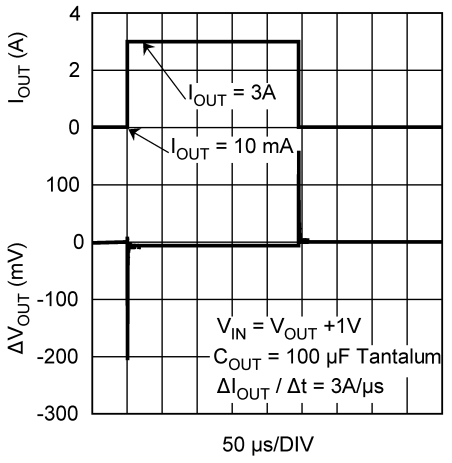
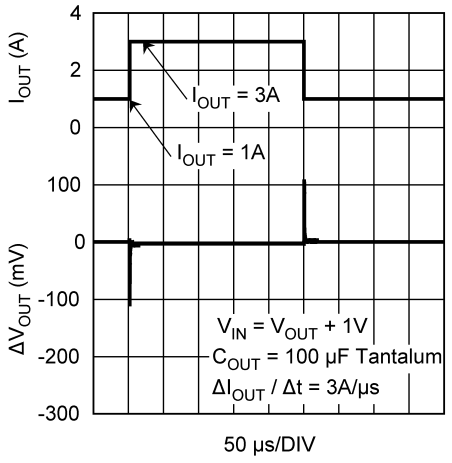
Load Transient Response, C_{OUT} = 100 µF Tantalum



20131185

Load Transient Response, C_{OUT} = 100 µF Tantalum



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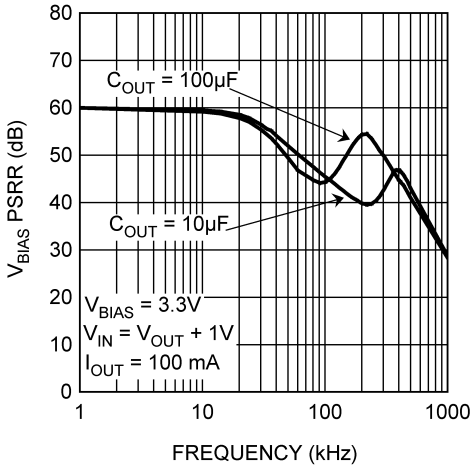
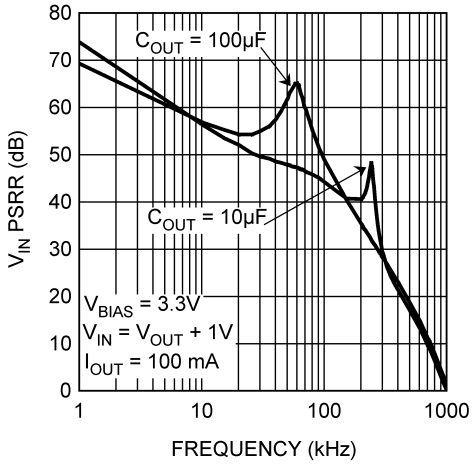
V_{BIAS} PSRR



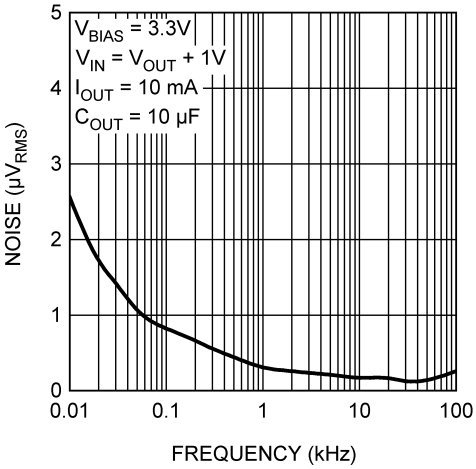
20131170

V_{IN} PSRR



20131171

Output Noise



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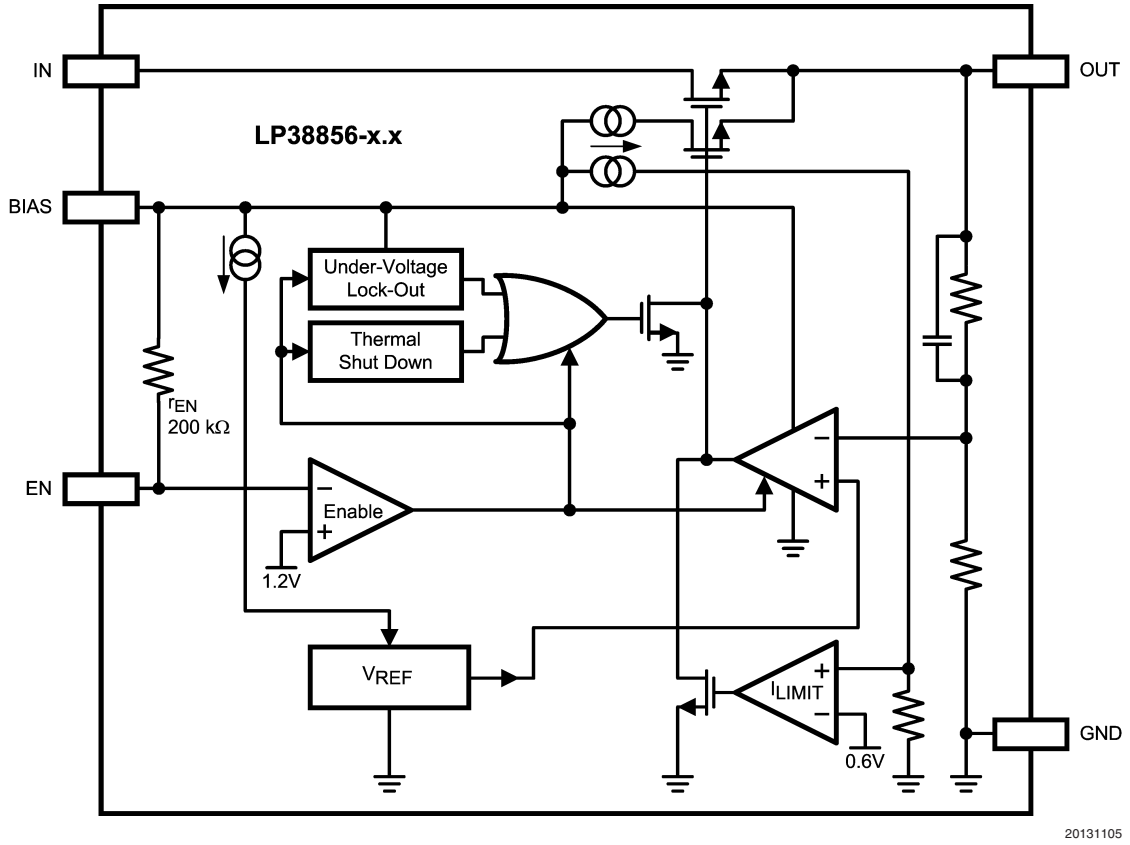
Block Diagram



Application Information

EXTERNAL CAPACITORS

To assure regulator stability, capacitors are required on the input, output and bias pins as shown in the Typical Application Circuit.

Output Capacitor

A minimum output capacitance of 10 µF, ceramic, is required for stability. The amount of output capacitance can be increased without limit. The output capacitor must be located less than 1 cm from the output pin of the IC and returned to the device ground pin with a clean analog ground.

Only high quality ceramic types such as X5R or X7R should be used, as the Z5U and Y5F types do not provide sufficient capacitance over temperature.

Tantalum capacitors will also provide stable operation across the entire operating temperature range. However, the effects of ESR may provide variations in the output voltage during fast load transients. Using the minimum recommended 10 µF ceramic capacitor at the output will allow unlimited capacitance, Tantalum and/or Aluminum, to be added in parallel.

Input Capacitor

The input capacitor must be at least 10 µF, but can be increased without limit. It's purpose is to provide a low source impedance for the regulator input. A ceramic capacitor, X5R or X7R, is recommended.

Tantalum capacitors may also be used at the input pin. There is no specific ESR limitation on the input capacitor (the lower, the better).

Aluminum electrolytic capacitors can be used, but are not recommended as their ESR increases very quickly at cold temperatures. They are not recommended for any application where the ambient temperature falls below 0˚C.

Bias Capacitor

The capacitor on the bias pin must be at least 1 µF. It can be any good quality capacitor (ceramic is recommended).

INPUT VOLTAGE

The input voltage (V_{IN}) is the high current external voltage rail that will be regulated down to a lower voltage, which is applied to the load. The input voltage must be at least V_{OUT} + V_{DO}, and no higher than whatever value is used for V_{BIAS}.

BIAS VOLTAGE

The bias voltage (V_{BIAS}) is a low current external voltage rail required to bias the control circuitry and provide gate drive for the N-FET pass transistor. The bias voltage must be in the range of 3.0V to 5.5V to ensure proper operation of the device.

UNDER VOLTAGE LOCKOUT

The bias voltage is monitored by a circuit which prevents the device from functioning when the bias voltage is below the Under-Voltage Lock-Out (UVLO) threshold of approximately 2.45V.

As the bias voltage rises above the UVLO threshold the device control circuitry become active. There is approximately 150 mV of hysteresis built into the UVLO threshold to provide noise immunity.

When the bias voltage is between the UVLO threshold and the Minimum Operating Rating value of 3.0V the device will be functional, but the operating parameters will not be within the guaranteed limits.

SUPPLY SEQUENCING

There is no requirement for the order that V_{IN} or V_{BIAS} are applied or removed. However, the output voltage cannot be guaranteed until both V_{IN} and V_{BIAS} are within the range of guaranteed operating values.

If used in a dual-supply system where the regulator load is returned to a negative supply, the output pin must be diode clamped to ground. A Schottky diode is recommend for this diode clamp.

REVERSE VOLTAGE

A reverse voltage condition will exist when the voltage at the output pin is higher than the voltage at the input pin. Typically this will happen when V_{IN} is abruptly taken low and C_{OUT} continues to hold a sufficient charge such that the input to output voltage becomes reversed.

The NMOS pass element, by design, contains no body diode. This means that, as long as the gate of the pass element is not driven, there will not be any reverse current flow through the pass element during a reverse voltage event. The gate of the pass element is not driven when V_{BIAS} is below the UVLO threshold.

When V_{BIAS} is above the UVLO threshold the control circuitry is active and will attempt to regulate the output voltage. Since the input voltage is less than the output voltage the control circuit will drive the gate of the pass element to the full V_{BIAS} potential when the output voltage begins to fall. In this condition, reverse current will flow from the output pin to the input pin, limited only by the $R_{DS(ON)}$ of the pass element and the output to input voltage differential. This condition is outside the guaranteed operating range and should be avoided.

ENABLE OPERATION

The Enable pin (EN) provides a mechanism to enable, or disable, the regulator output stage. The Enable pin has an internal pull-up, through a typical 200 kΩ resistor, to V_{BIAS}.

If the Enable pin is actively driven, pulling the Enable pin above the V_{EN} threshold of 1.25V (typical) will turn the regulator output on, while pulling the Enable pin below the V_{EN} threshold will turn the regulator output off. There is approximately 100 mV of hysteresis built into the Enable threshold provide noise immunity.

If the Enable function is not needed this pin should be left open, or connected directly to V_{BIAS}. If the Enable pin is left open, stray capacitance on this pin must be minimized, otherwise the output turn-on will be delayed while the stray capacitance is charged through the internal resistance (r_{EN}).

POWER DISSIPATION AND HEAT-SINKING

A heat-sink may be required depending on the maximum power dissipation and maximum ambient temperature of the application. Under all possible conditions, the junction temperature must be within the range specified under operating conditions.

The total power dissipation of the device is the sum of three different points of dissipation in the device.

The first part is the power that is dissipated in the NMOS pass element, and can be determined with the formula:

Application Information (Continued)

$$P_{D(PASS)} = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (1)$$

The second part is the power that is dissipated in the bias and control circuitry, and can be determined with the formula:

$$P_{D(BIAS)} = V_{BIAS} \times I_{GND(BIAS)} \quad (2)$$

where $I_{GND(BIAS)}$ is the portion of the operating ground current of the device that is related to V_{BIAS}.

The third part is the power that is dissipated in portions of the output stage circuitry, and can be determined with the formula:

$$P_{D(IN)} = V_{IN} \times I_{GND(IN)} \quad (3)$$

where $I_{GND(IN)}$ is the portion of the operating ground current of the device that is related to V_{IN}.

The total power dissipation is then:

$$P_D = P_{D(PASS)} + P_{D(BIAS)} + P_{D(IN)} \quad (4)$$

The maximum allowable junction temperature rise (ΔT_J) depends on the maximum anticipated ambient temperature ($T_{A(MAX)}$) for the application, and the maximum allowable operating junction temperature ($T_{J(MAX)}$):

$$\Delta T_J = T_{J(MAX)} - T_{A(MAX)} \quad (5)$$

The maximum allowable value for junction to ambient Thermal Resistance, θ_{JA}, can be calculated using the formula:

$$\theta_{JA} \leq \frac{\Delta T_J}{P_D} \quad (6)$$

The LP38856 is available in TO-220 and TO-263 packages. The thermal resistance in the application depends on amount of copper area or heat-sink, and on air flow. If the maximum allowable value of θ_{JA} calculated above is ≥ 60 ˚C/W for TO-220 package and ≥ 60 ˚C/W for TO-263 package no heat-sink is needed since the package alone can dissipate enough heat to satisfy these requirements. If the value needed for allowable θ_{JA} falls below these limits, a heat-sink is required.

Heat-Sinking The TO-220 Package

The TO-220 package has a θ_{JA} rating of 60˚C/W, and a θ_{JC} rating of 3˚C/W. These ratings are for the package only, no additional heat-sinking, and with no airflow.

The thermal resistance of a TO-220 package can be reduced by attaching it to a heat-sink or a copper plane on a PC board. If a copper plane is to be used, the values of θ_{JA} will be same as shown in next section for TO-263 package.

The heat-sink to be used in the application should have a heat-sink to ambient thermal resistance, θ_{HA}:

$$\theta_{HA} \leq \theta_{JA} - (\theta_{CH} + \theta_{JC}) \quad (7)$$

where θ_{JA} is the required total thermal resistance from the junction to the ambient air, θ_{CH} is the thermal resistance from the case to the surface of the heat sink, and θ_{JC} is the thermal resistance from the junction to the surface of the case.

For this equation, θ_{JC} is about 3˚C/W for a TO-220 package. The value for θ_{CH} depends on method of attachment, insulator, etc. θ_{CH} varies between 1.5˚C/W to 2.5˚C/W. Consult the heat-sink manufacturer datasheet for details and recommendations.

Heat-Sinking The TO-263 Package

The TO-263 package has a θ_{JA} rating of 60˚C/W, and a θ_{JC} rating of 3˚C/W. These ratings are for the package only, no additional heat-sinking, and with no airflow.

The TO-263 package uses the copper plane on the PCB as a heat-sink. The tab of this package is soldered to the copper plane for heat-sinking. The graph below shows a curve for the θ_{JA} of TO-263 package for different copper area sizes, using a typical PCB with 1 ounce copper and no solder mask over the copper area for heat-sinking.

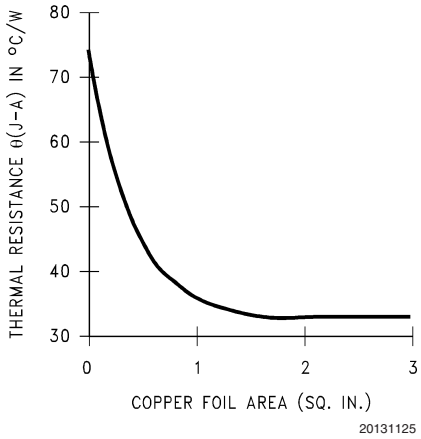


FIGURE 1. θ_{JA} vs Copper (1 Ounce) Area for the TO-263 package

As shown in *Figure 1*, increasing the copper area beyond 1 square inch produces very little improvement. The minimum value for θ_{JA} for the TO-263 package mounted to a PCB is 32˚C/W.

Figure 2 shows the maximum allowable power dissipation for TO-263 packages for different ambient temperatures, assuming θ_{JA} is 35˚C/W and the maximum junction temperature is 125˚C.

Application Information (Continued)

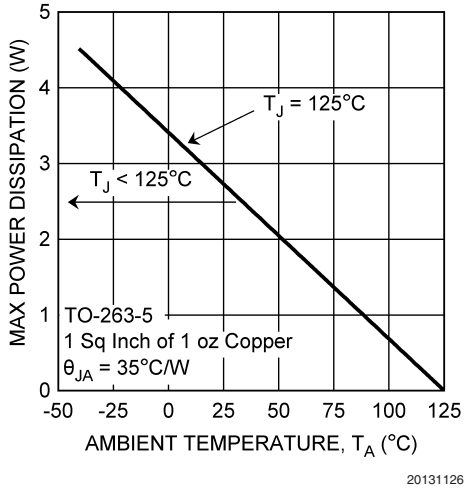
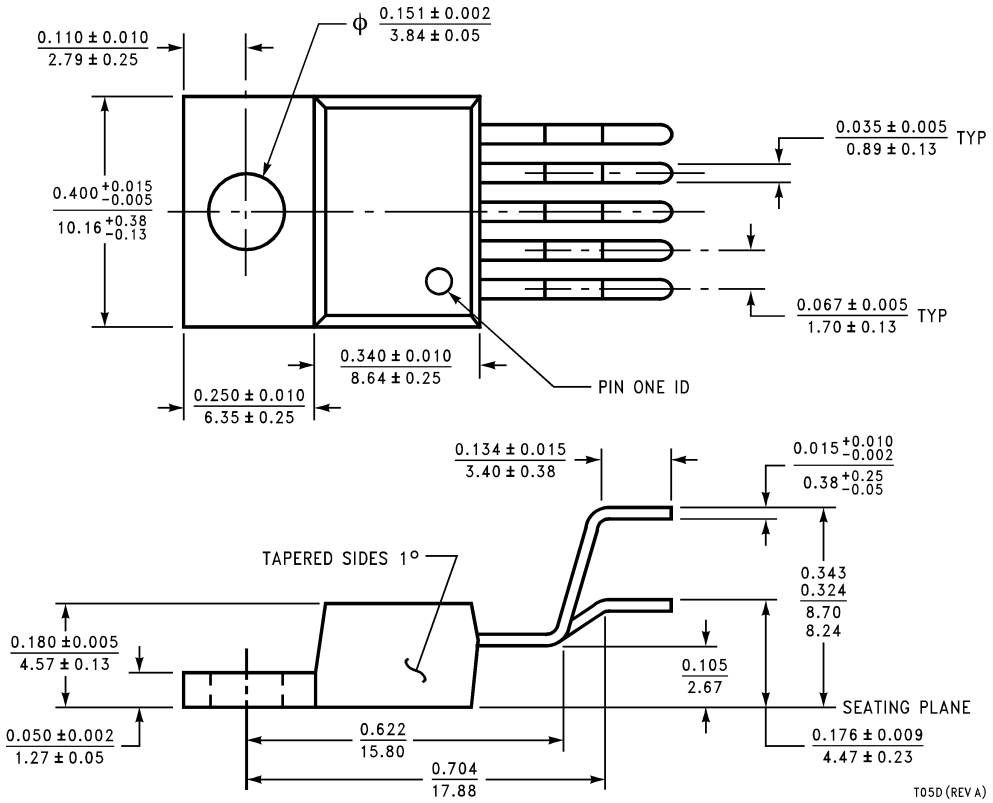
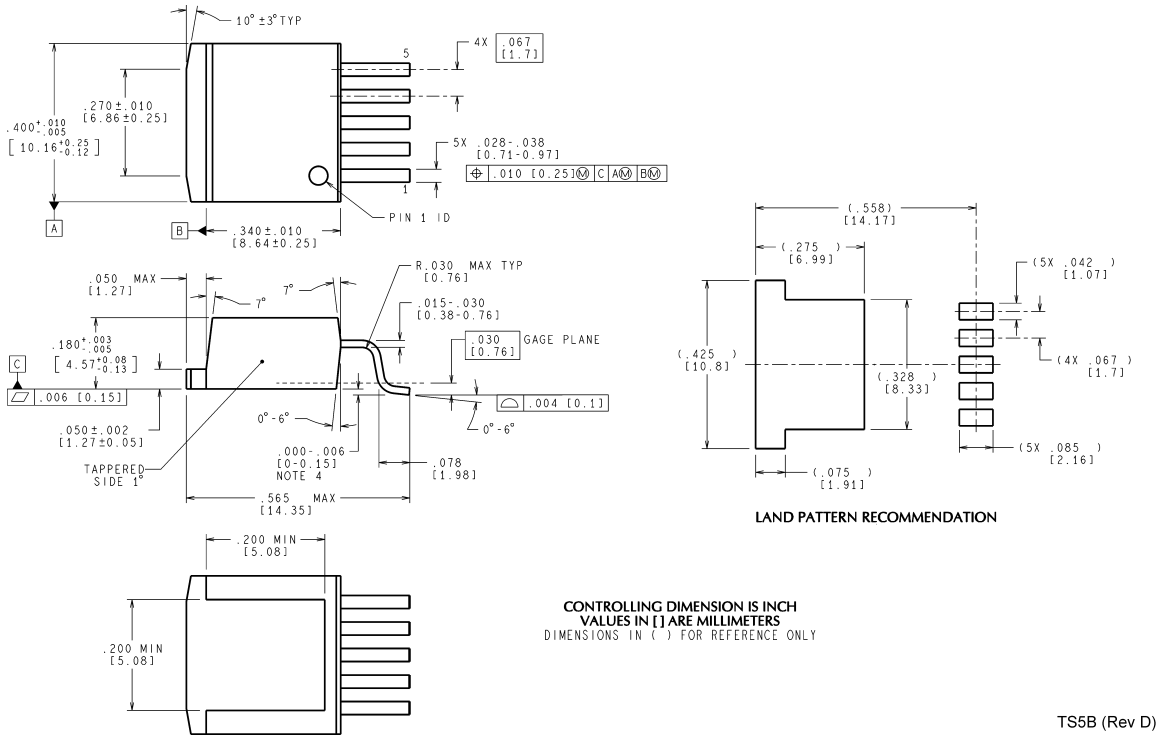


FIGURE 2. Maximum Power Dissipation vs Ambient Temperature for TO-263 package

Physical Dimensions inches (millimeters) unless otherwise noted



TO220 5-lead, Molded, Stagger Bend Package (TO220-5)
NS Package Number T05D



TO263 5-Lead, Molded, Surface Mount Package (TO263-5)
NS Package Number TS5B

Notes

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